



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)		Atty Docket No. UNTYP019 Applicant: Rinerson et al. Filing Date August 4, 2003	Application No.: 10/604,606 Group 2813
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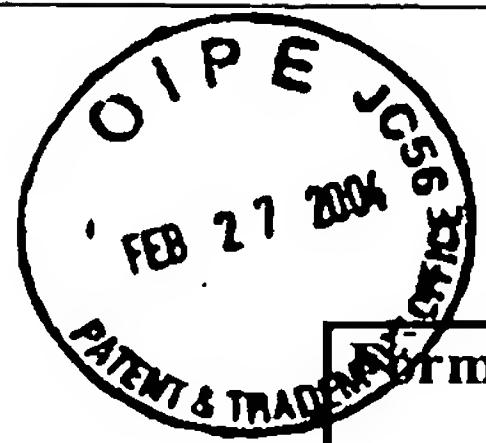
U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>pr</i>	A	6,204,139	2001-03-20	Liu et al.			

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>DS</i>	B	Basun, S. A. et al., "Photoinduced Phenomena in $Sr_{1-x}Ca_xTiO_3$, $0 \leq x \leq 0.12$ ", Ferroelectrics, Vol. 183, 1996, 255-264.
	C	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
	D	Gerstner E.G. et al., "Nonvolatile memory effects in nitrogen doped tetrahedral amorphous carbon thin films", Journal of Applied Physics, Vol. 84, No. 10, 15 November 1998, 5647-5651.
	E	Koidl, P. et al., "Photochromism in Ni-doped $SrTiO_3$ ", Physical Review B, Vol. 14, No. 7, 1 October 1976, 2703-2708.
	F	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
<i>✓</i>	G	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped $SrTiO_3$ single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner	<i>RLS</i>	
	Date Considered	
	<i>5/1/05</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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UNTYP019

Applicant:

Rinerson et al.

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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>DS</i>	A	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
<i>DS</i>	B	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
Examiner		<i>✓ ✓</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.